

**In the Claims:**

1. (Original) A magnetic memory comprising:  
a plurality of digit lines;  
a plurality of bit lines, wherein the digit lines and the bit lines intersect each other at an oblique angle; and  
magnetic tunnel junctions (MTJs) between the bit lines and the digit lines.
2. (Original) The magnetic memory of claim 1, wherein the digit lines and the bit lines intersect each other at an oblique angle of between 15° to 75°.
3. (Original) The magnetic memory of claim 1, wherein the MTJs are directly connected to the bit lines, and are spaced apart from the digit lines.
4. (Original) The magnetic memory of claim 1, further comprising a plurality of cell transistors, wherein the cell transistors are arrayed along a row direction and a column direction, wherein the cell transistors comprise a gate electrode, a source region and a drain region, and wherein the gate electrodes of the cell transistors are connected to each other through a plurality of word lines.
5. (Original) The magnetic memory of claim 4, wherein the digit lines are parallel to the word lines, and the bit lines intersect the word lines at an oblique angle.
6. (Original) The magnetic memory of claim 5, wherein the bit lines diagonally connect the drain regions of the cell transistors to each other.
7. (Original) The magnetic memory of claim 5, wherein the bit lines zigzag to connect the drain regions of the cell transistors to each other.

8. (Original) The magnetic memory of claim 4, wherein the bit lines intersect the word lines perpendicularly, and the digit lines intersect the word lines at an oblique angle.

9. (Original) The magnetic memory of claim 8, wherein the digit lines diagonally intersect the cell transistors.

10. (Original) The magnetic memory of claim 8, wherein the digit lines intersect the cell transistors in a zigzag pattern.

11. (Original) The magnetic memory of claim 1, wherein the MTJs comprise a pinning layer, a fixed layer, an insulating layer and a free layer.

12. (Original) The magnetic memory of claim 11, wherein the fixed layer comprises a lower ferromagnetic film, a ruthenium film and an upper ferromagnetic film.

13. (Original) The magnetic memory of claim 1, wherein the MTJs have a rectangular shape.

14. (Original) The magnetic memory of claim 1, wherein the MTJs have a parallelogram shape.

15. (Original) The magnetic memory of claim 1, wherein the MTJs have a parallelogram shape with rounded corner portions.

16-28. (Canceled).